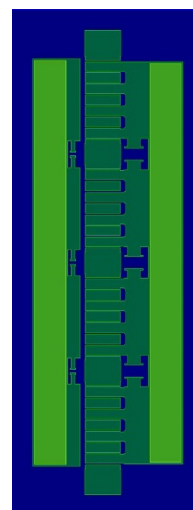


Product Overview

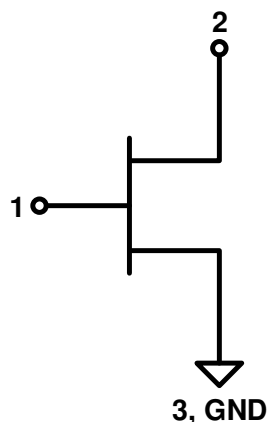
The Qorvo TGF2934 is a 14 W (P_{3dB}) discrete GaN on SiC HEMT which operates from DC to 25 GHz and 28 V supply. The device is constructed with Qorvo's proven QGaN15 process. The device can support pulsed, CW, and linear operations.

Lead-free and ROHS compliant



1.457 x 0.551 x 0.100 mm

Functional Block Diagram



Key Features

- Frequency: DC to 25 GHz
 - Output Power (P_{3dB})¹: 14 W
 - Linear Gain¹: 14 dB
 - Typical PAE_{3dB}¹: 49%
 - Typical Noise Figure¹: 1.5 dB
 - Operating Voltage: 28 V
 - CW and Pulse capable
 - Non-linear & Noise Models available
- Note 1: @ 10 GHz

Applications

- Defense and Aerospace
- Broadband wireless
- Low noise amplifier

Ordering info

Part No.	ECCN	Description
TGF2934	3A001b.3.b	DC–25 GHz, 28 V, 3.5 W GaN RF Transistor

Absolute Maximum Ratings¹

Parameter	Rating	Units
Breakdown Voltage, BV_{DG}	+60	V
Gate Voltage Range, V_G	-7 to +1.5	V
Drain Current, $I_{D_{MAX}}$	4	A
Gate Current Range, I_G	See page 20.	mA
Power Dissipation, CW, P_{DISS}^2	17.4	W
RF Input Power, CW, 10 GHz, $T = 25\text{ }^{\circ}\text{C}$	+33	dBm
Channel Temperature, T_{CH}	275	$^{\circ}\text{C}$
Mounting Temperature (30 Seconds)	320	$^{\circ}\text{C}$
Storage Temperature	-65 to +150	$^{\circ}\text{C}$

Notes:

1. Operation of this device outside the parameter ranges given above may cause permanent damage.
2. Base temperature at 85 $^{\circ}\text{C}$

Recommended Operating Conditions¹

Parameter	Min	Typ	Max	Units
Operating Temp. Range	-40	+25	+85	$^{\circ}\text{C}$
Drain Voltage Range, V_D	+12	+20	+29.5	V
Drain Bias Current, I_{DQ}	80	160	320	mA
Drain Current, I_D	–	1000	–	mA
Gate Voltage, V_G^3	–	-2.8	–	V
Channel Temperature (T_{CH})	–	–	250	$^{\circ}\text{C}$
Power Dissipation, CW (P_D) ²	–	–	15.8	W

Notes:

1. Electrical performance is measured under conditions noted in the electrical specifications table. Specifications are not guaranteed over all recommended operating conditions.
2. Package base at 85 $^{\circ}\text{C}$
3. To be adjusted to desired I_{DQ}

Model Load Pull Performance – Power Tuned¹

Parameter	Typical Values								Units
Frequency, F	3		6		10		18		GHz
Drain Voltage, V _D	20	28	20	28	20	28	20	28	V
Drain Bias Current, I _{DQ}	160	160	160	160	160	160	160	160	mA
Output Power at 3dB compression, P _{3dB}	40.7	41.6	40.8	41.7	40.8	41.5	39.5	41.8	dBm
Power Added Efficiency at 3dB compression, PAE _{3dB}	56.9	51.7	55.0	51.3	51.4	49.3	43.7	44.9	%
Gain at 3dB compression, G _{3dB}	18.7	21.5	13.3	15.4	8.9	11.2	5.9	6.9	dB
Load Reflection Coefficient ⁽²⁾ , Γ_L	0.63 $\angle$ 162°	0.45 $\angle$ 153°	0.73 $\angle$ 164°	0.67 $\angle$ 153°	0.82 $\angle$ 166°	0.85 $\angle$ 159°	0.92 $\angle$ 167°	0.92 $\angle$ 167°	--

Notes:

1. CW, bondwires not included
2. Characteristic Impedance, Z₀ = 50 Ω .

Model Load Pull Performance – Efficiency Tuned¹

Parameter	Typical Values								Units
Frequency, F	3		6		10		18		GHz
Drain Voltage, V _D	20	28	20	28	20	28	20	28	V
Drain Bias Current, I _{DQ}	160	160	160	160	160	160	160	160	mA
Output Power at 3dB compression, P _{3dB}	40.2	41.3	40.1	41.7	40.8	41.5	39.5	41.8	dBm
Power Added Efficiency at 3dB compression, PAE _{3dB}	58	53.1	57.5	51.3	51.4	49.3	43.7	44.9	%
Gain at 3dB compression, G _{3dB}	18.4	23.0	13.6	15.4	8.9	11.2	5.9	6.9	dB
Load Reflection Coefficient ⁽²⁾ , Γ_L	0.67 $\angle$ 153°	0.50 $\angle$ 143°	0.76 $\angle$ 157°	0.67 $\angle$ 153°	0.82 $\angle$ 166°	0.85 $\angle$ 159°	0.92 $\angle$ 167°	0.92 $\angle$ 167°	--

Notes:

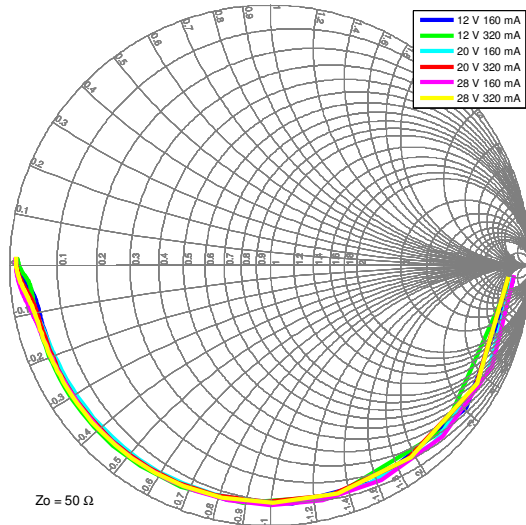
1. CW, bondwires not included
2. Characteristic Impedance, Z₀ = 50 Ω .

Model S-parameters¹

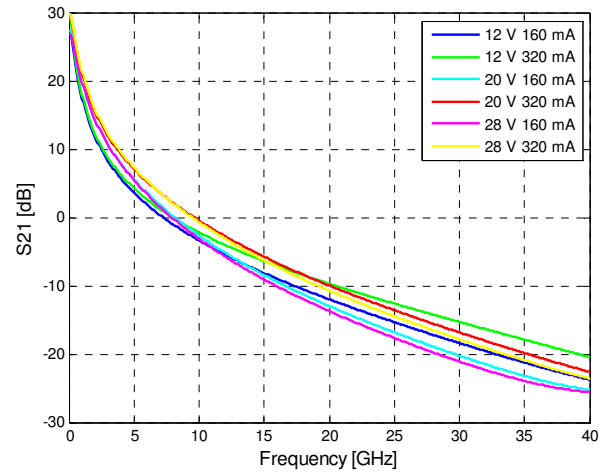
Notes:

1. Bondwires are not included. T = 25 °C.

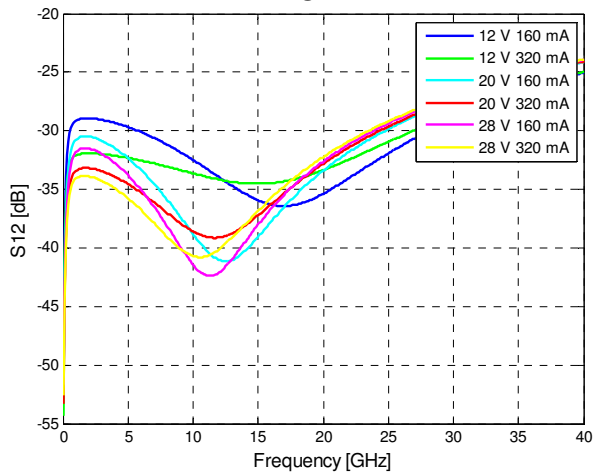
S11 from 0.01 GHz to 40 GHz



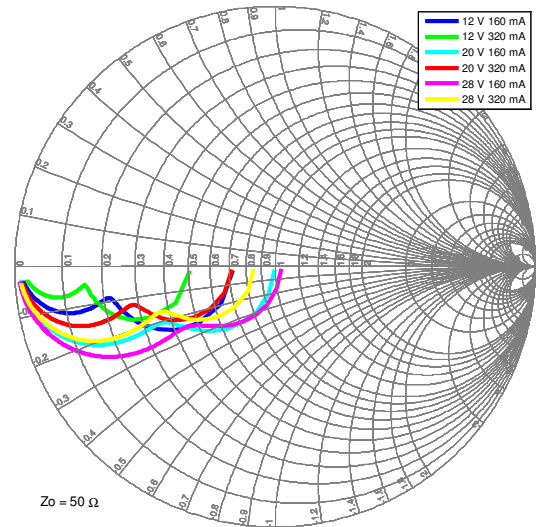
S21



S12



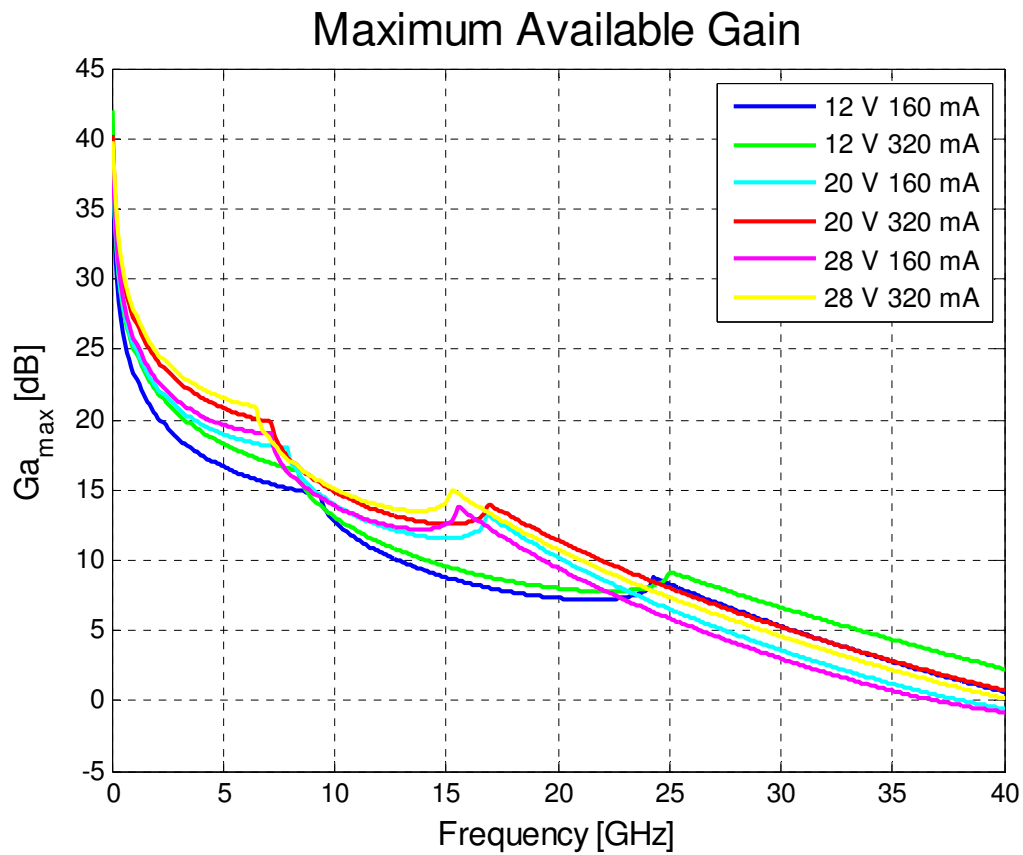
S22 from 0.01 GHz to 40 GHz



Model Maximum Available Gain¹

Notes:

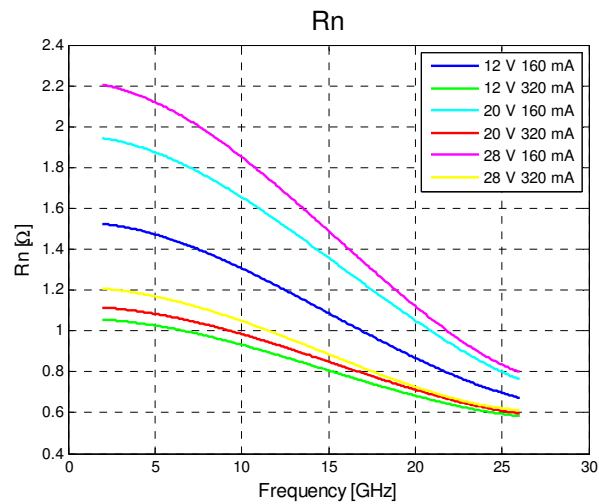
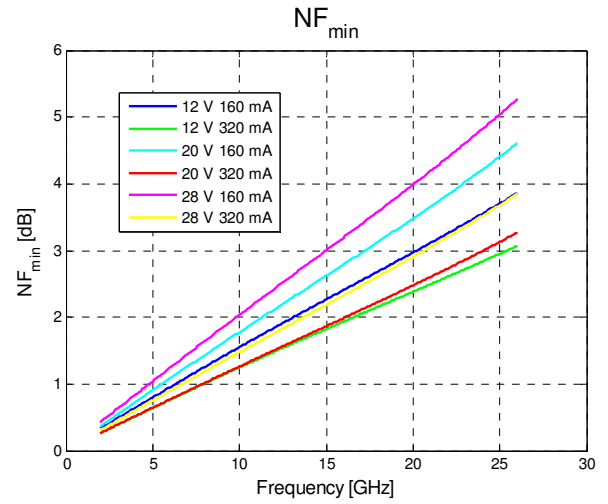
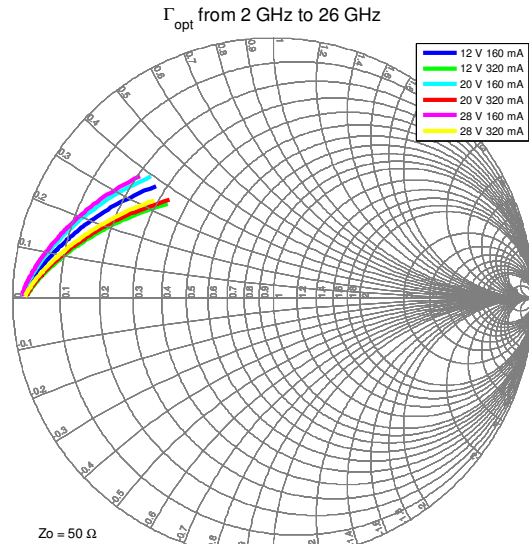
1. Bondwires are not included. T = 25 °C.



Model Noise¹

Notes:

1. Bondwires are not included. T = 25 °C.

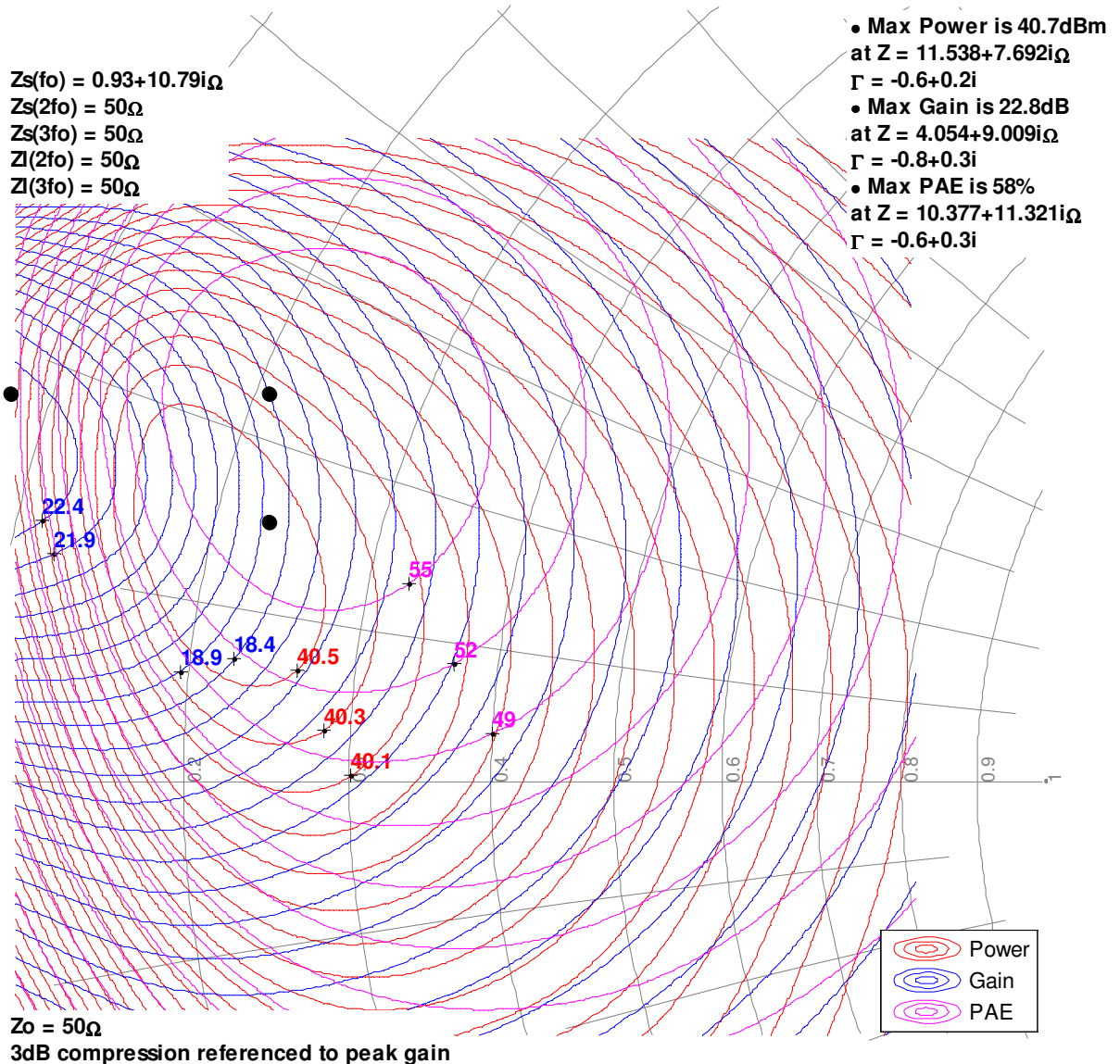


Model Load-Pull Smith Charts^{1, 2, 3}

Notes:

1. Test Conditions: $V_D = 20$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

3GHz, Load-pull



Model Load-Pull Smith Charts^{1, 2}

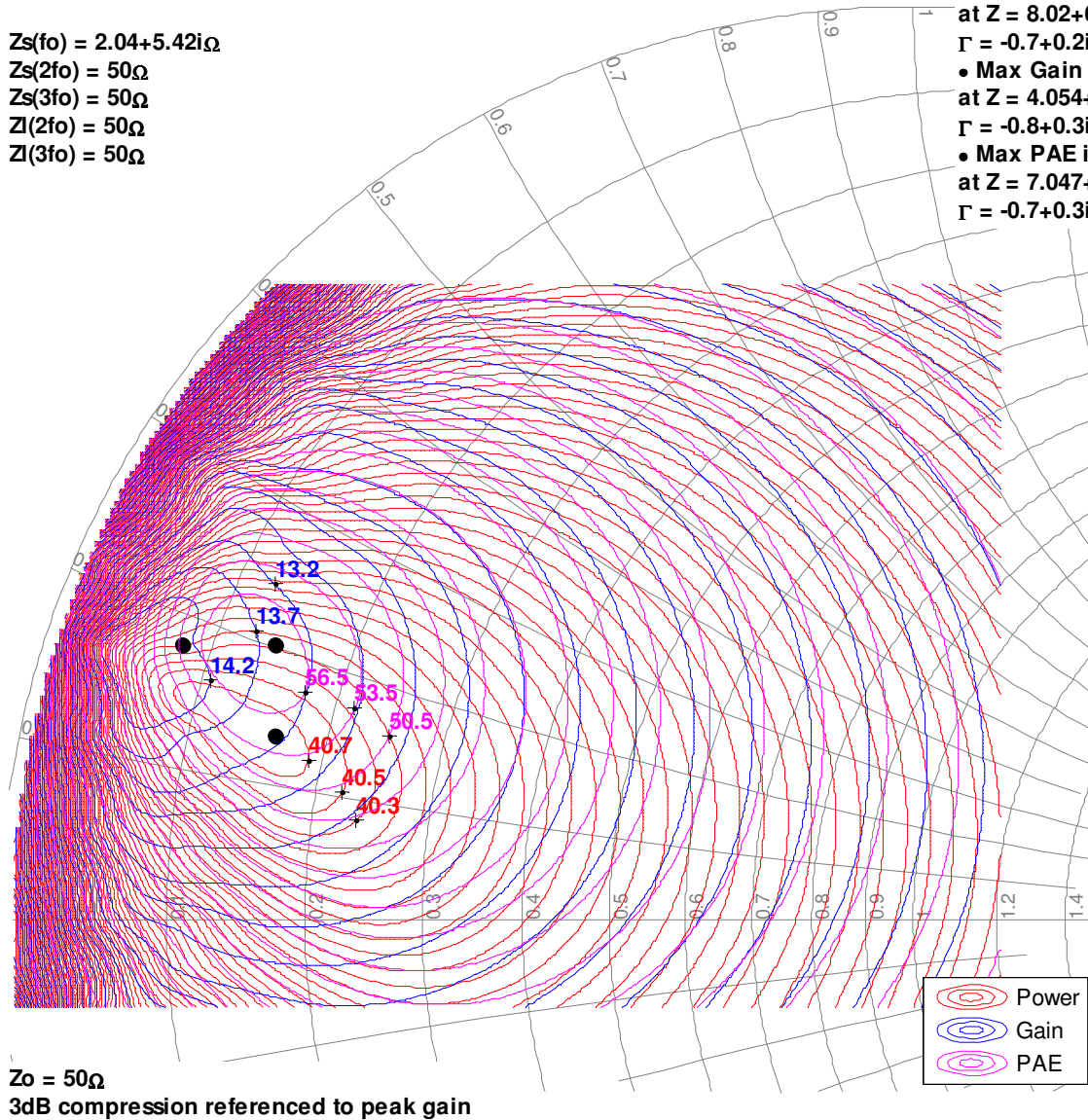
Notes:

1. Test Conditions: $V_D = 20$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

6GHz, Load-pull

$Z_s(f_0) = 2.04 + 5.42i\Omega$
 $Z_s(2f_0) = 50\Omega$
 $Z_s(3f_0) = 50\Omega$
 $Z_l(2f_0) = 50\Omega$
 $Z_l(3f_0) = 50\Omega$

- Max Power is 40.8dBm
at $Z = 8.02 + 6.826i\Omega$
 $\Gamma = -0.7 + 0.2i$
- Max Gain is 14.3dB
at $Z = 4.054 + 9.009i\Omega$
 $\Gamma = -0.8 + 0.3i$
- Max PAE is 57.5%
at $Z = 7.047 + 10.067i\Omega$
 $\Gamma = -0.7 + 0.3i$



Model Load-Pull Smith Charts^{1, 2}

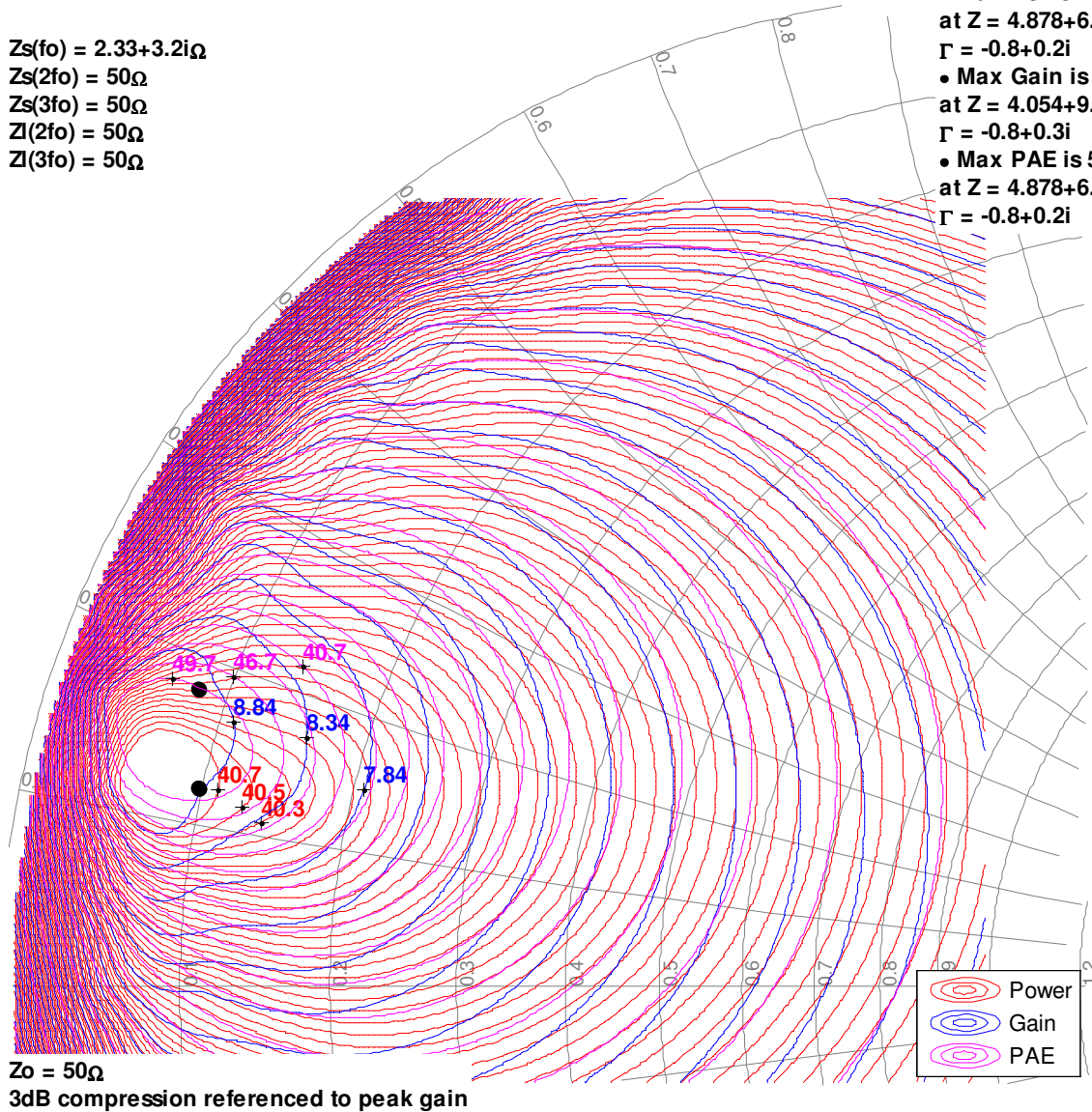
Notes:

1. Test Conditions: $V_D = 20$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

10GHz, Load-pull

$Z_s(f_0) = 2.33 + 3.2i\Omega$
 $Z_s(2f_0) = 50\Omega$
 $Z_s(3f_0) = 50\Omega$
 $Z_l(2f_0) = 50\Omega$
 $Z_l(3f_0) = 50\Omega$

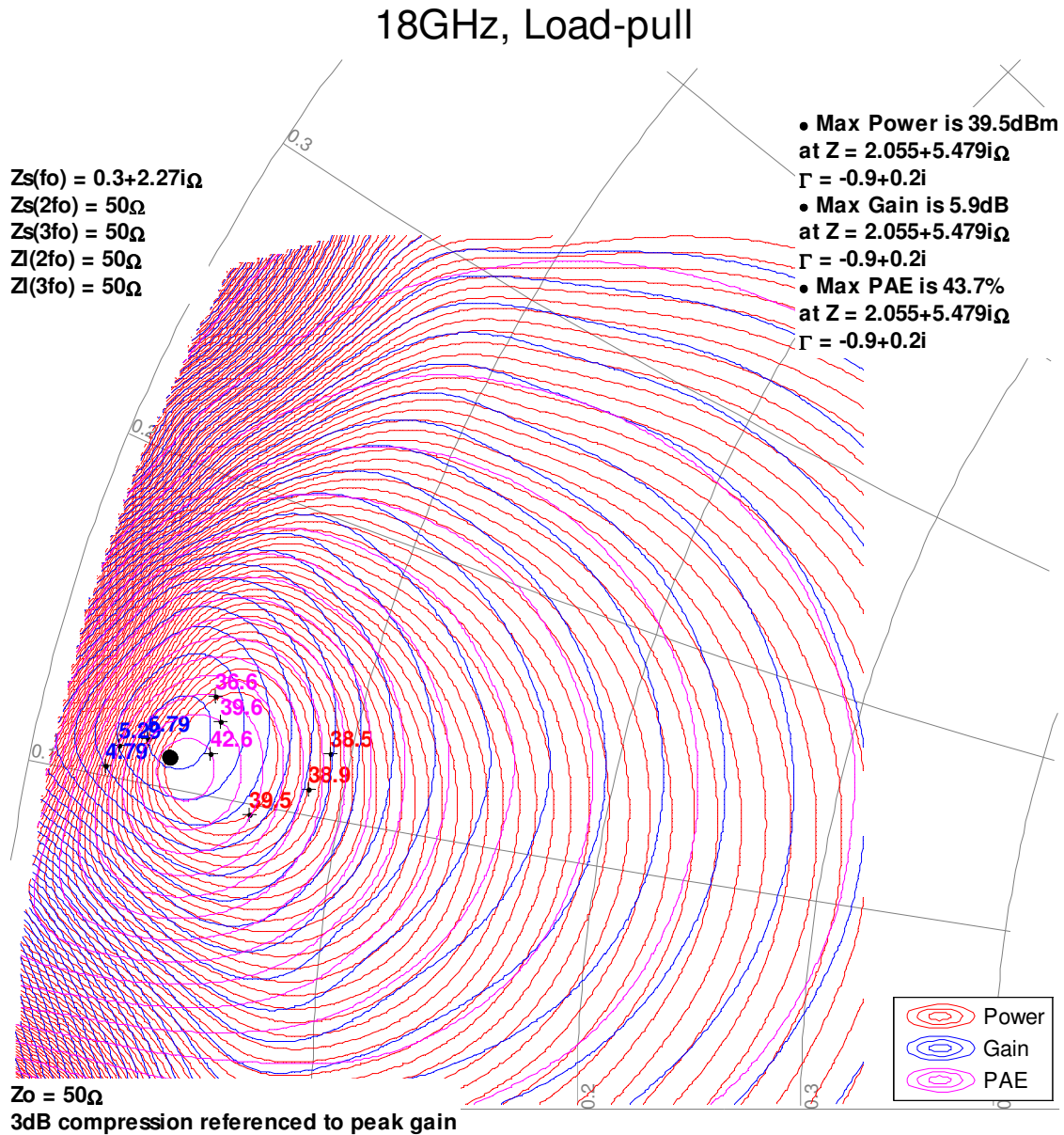
- Max Power is 40.8dBm at $Z = 4.878 + 6.097i\Omega$
 $\Gamma = -0.8 + 0.2i$
- Max Gain is 9dB at $Z = 4.054 + 9.009i\Omega$
 $\Gamma = -0.8 + 0.3i$
- Max PAE is 51.4% at $Z = 4.878 + 6.097i\Omega$
 $\Gamma = -0.8 + 0.2i$



Model Load-Pull Smith Charts^{1, 2}

Notes:

1. Test Conditions: $V_D = 20$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

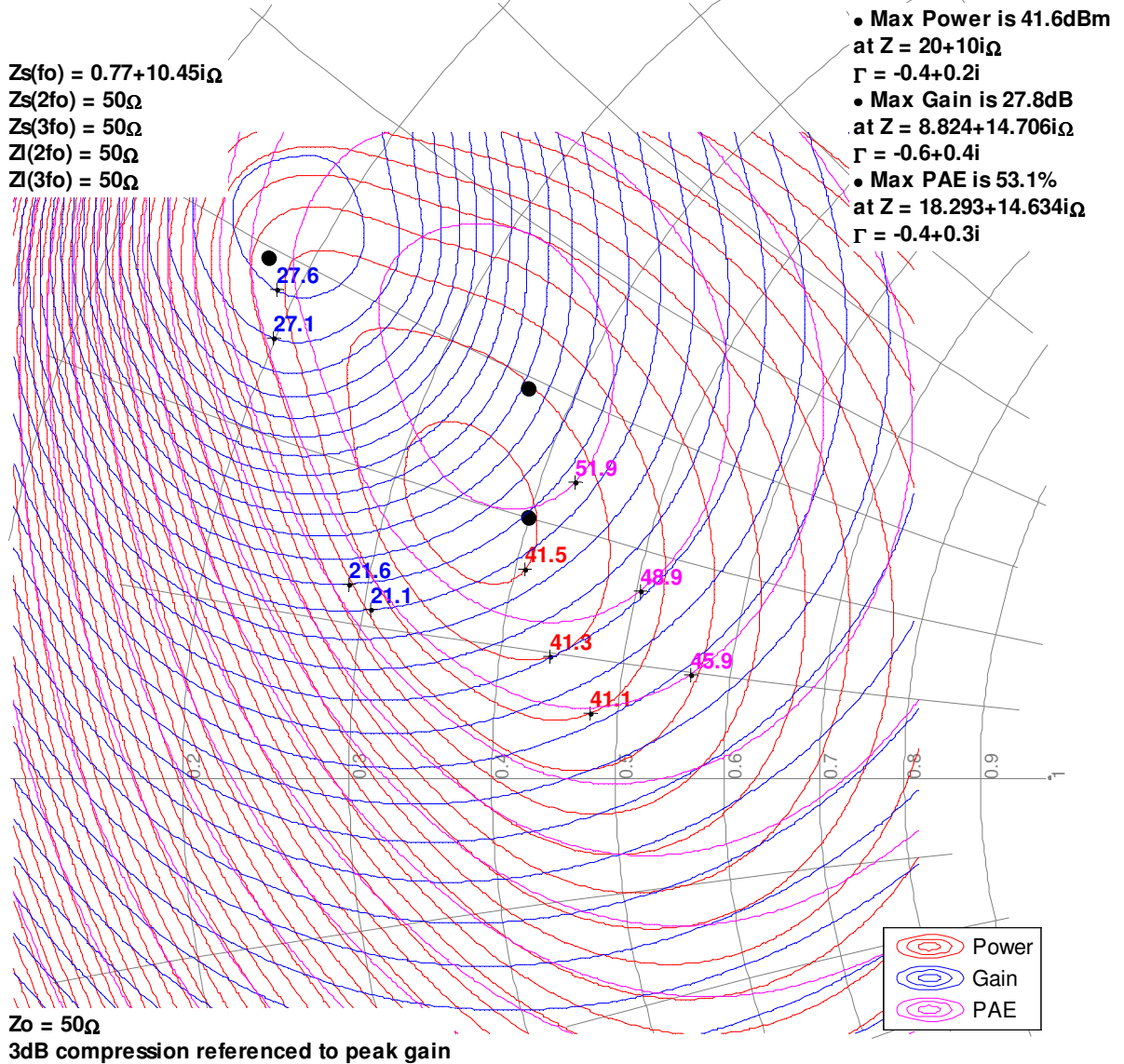


Model Load-Pull Smith Charts^{1,2}

Notes:

1. Test Conditions: $V_D = 28$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

3GHz, Load-pull



Model Load-Pull Smith Charts^{1, 2}

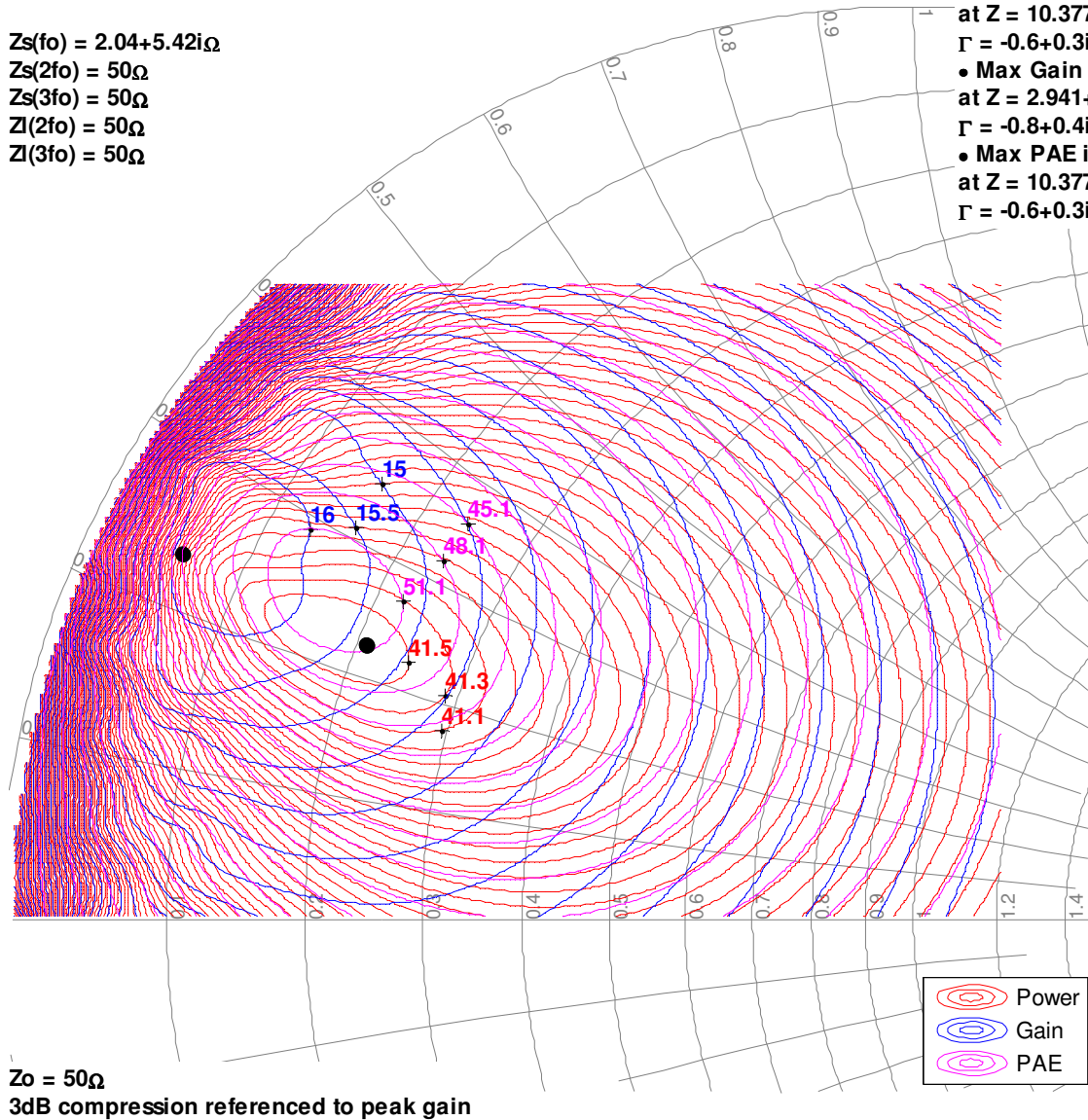
Notes:

1. Test Conditions: $V_D = 28$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

6GHz, Load-pull

$Z_s(f_0) = 2.04 + 5.42i\Omega$
 $Z_s(2f_0) = 50\Omega$
 $Z_s(3f_0) = 50\Omega$
 $Z_l(2f_0) = 50\Omega$
 $Z_l(3f_0) = 50\Omega$

- Max Power is 41.7dBm at $Z = 10.377 + 11.321i\Omega$
 $\Gamma = -0.6 + 0.3i$
- Max Gain is 16.4dB at $Z = 2.941 + 11.765i\Omega$
 $\Gamma = -0.8 + 0.4i$
- Max PAE is 51.4% at $Z = 10.377 + 11.321i\Omega$
 $\Gamma = -0.6 + 0.3i$



Model Load-Pull Smith Charts^{1, 2}

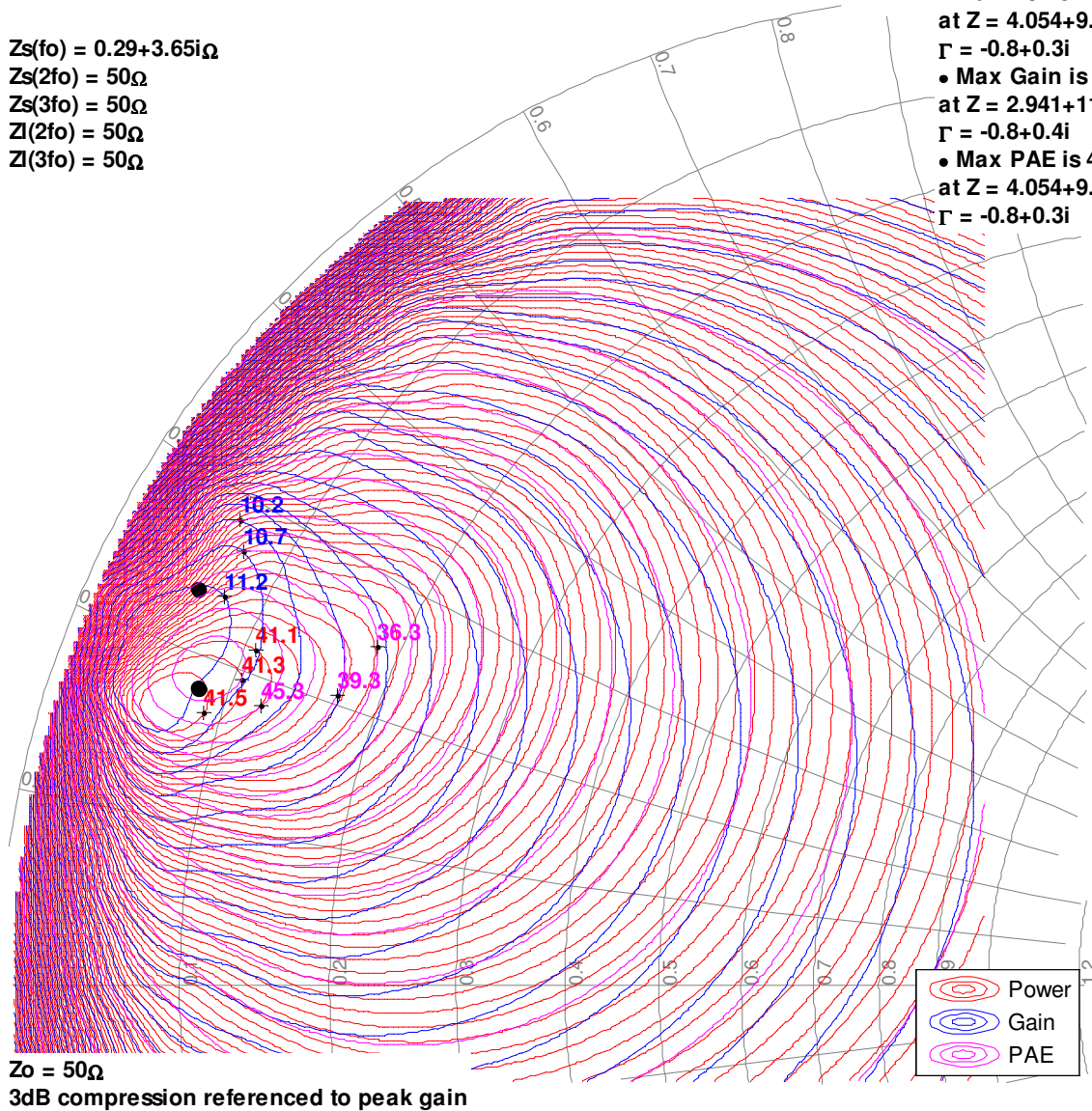
Notes:

1. Test Conditions: $V_D = 28$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

10GHz, Load-pull

$Z_S(f_0) = 0.29 + 3.65i\Omega$
 $Z_S(2f_0) = 50\Omega$
 $Z_S(3f_0) = 50\Omega$
 $Z_L(2f_0) = 50\Omega$
 $Z_L(3f_0) = 50\Omega$

- Max Power is 41.5dBm at $Z = 4.054 + 9.009i\Omega$
 $\Gamma = -0.8 + 0.3i$
- Max Gain is 11.3dB at $Z = 2.941 + 11.765i\Omega$
 $\Gamma = -0.8 + 0.4i$
- Max PAE is 49.1% at $Z = 4.054 + 9.009i\Omega$
 $\Gamma = -0.8 + 0.3i$

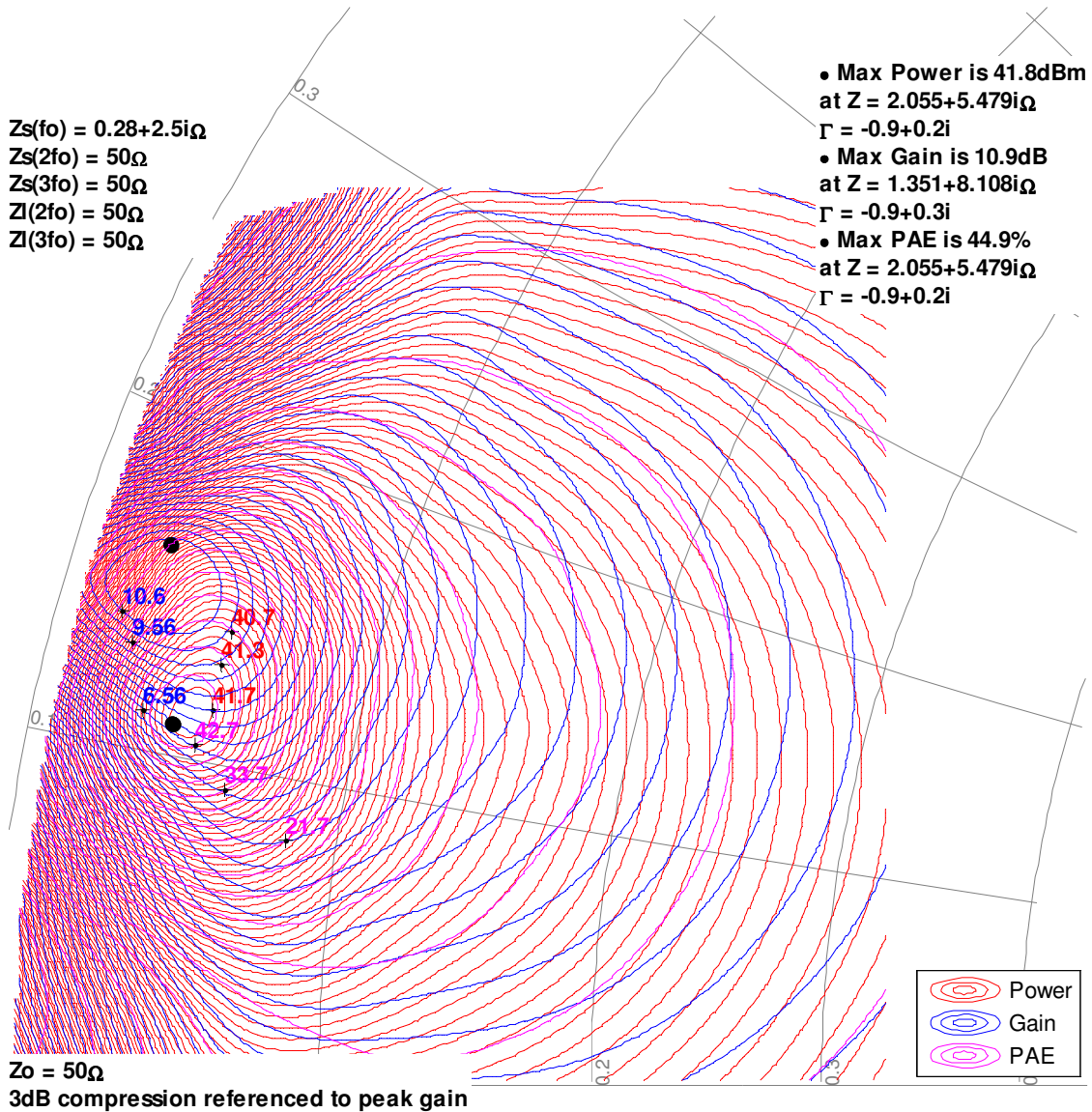


Model Load-Pull Smith Charts^{1, 2}

Notes:

1. Test Conditions: $V_D = 28$ V, $I_{DQ} = 160$ mA, CW, Bondwires not included
2. See page 22 for load pull reference planes where the performance was simulated.

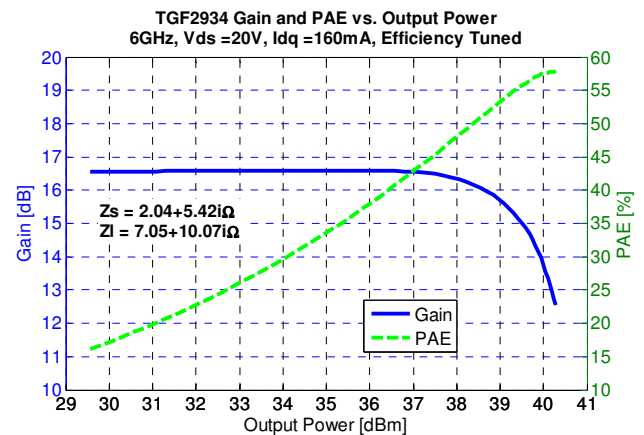
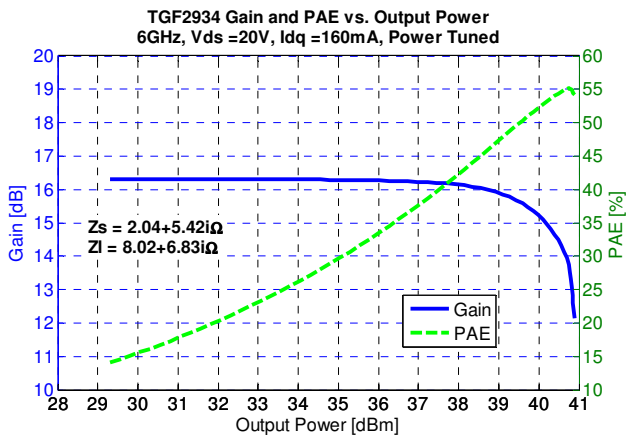
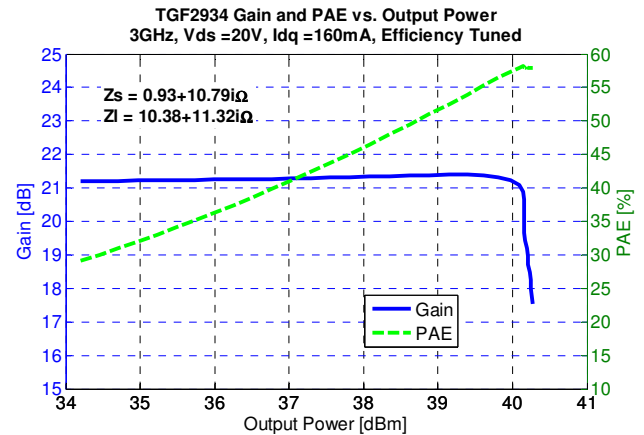
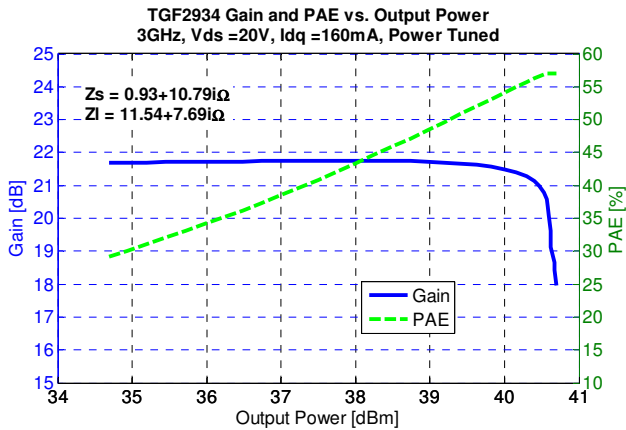
18GHz, Load-pull



Typical Model Performance – Load-Pull Drive-up^{1, 2}

Notes:

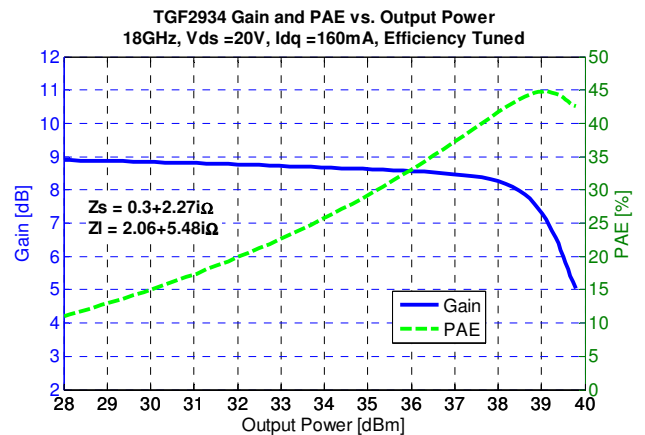
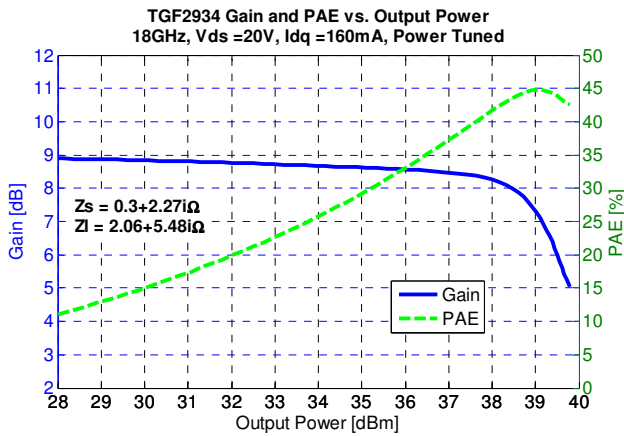
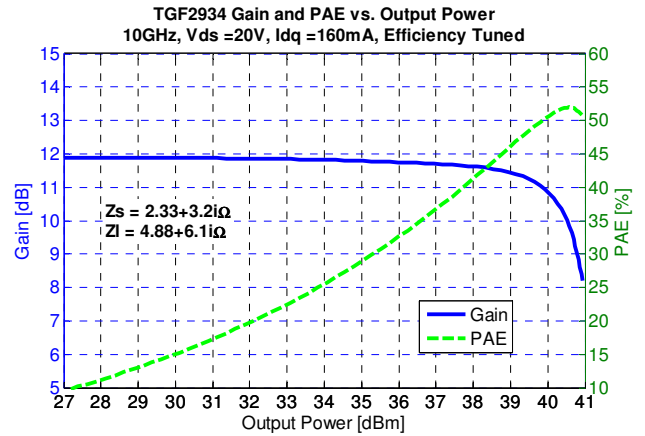
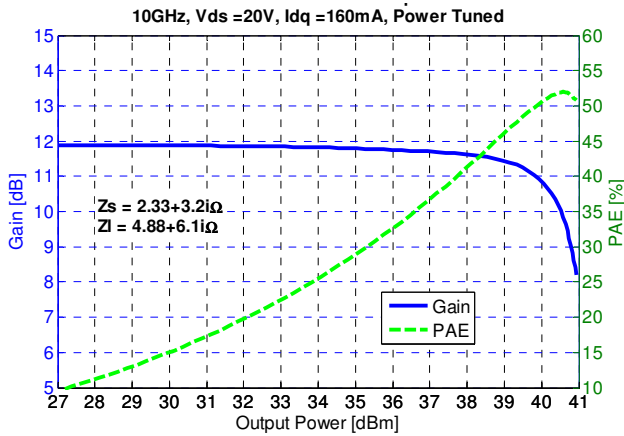
1. CW, Bondwires not included
2. See page 22 for load-pull and source-pull reference planes where the performance was measured.



Typical Model Performance – Load-Pull Drive-up^{1, 2}

Notes:

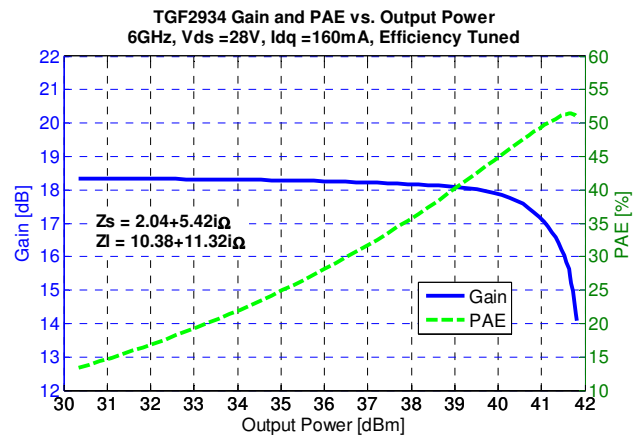
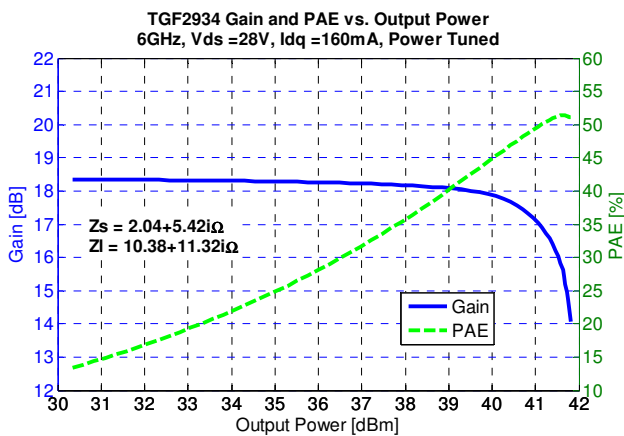
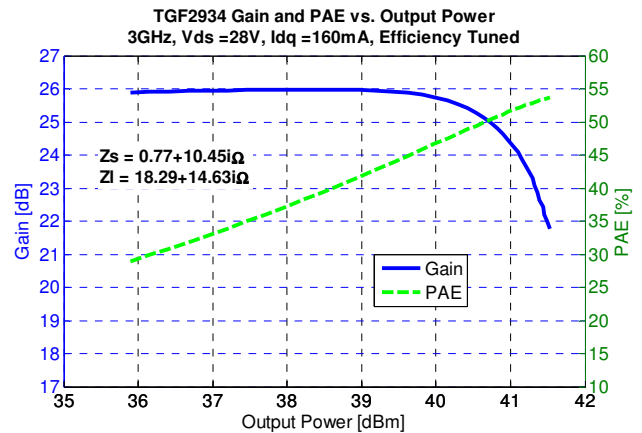
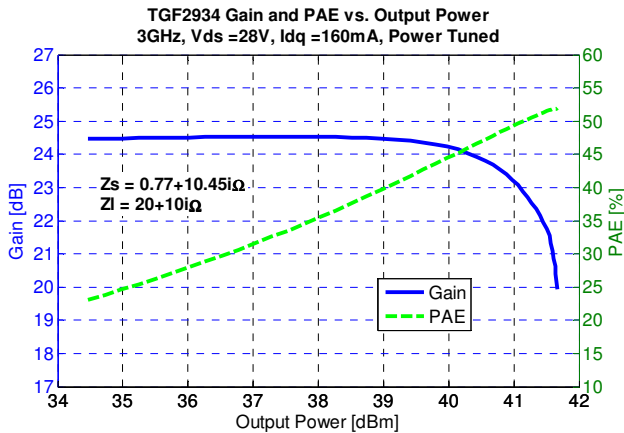
1. CW, Bondwires not included
2. See page 22 for load-pull and source-pull reference planes where the performance was measured.



Typical Model Performance – Load-Pull Drive-up^{1,2}

Notes:

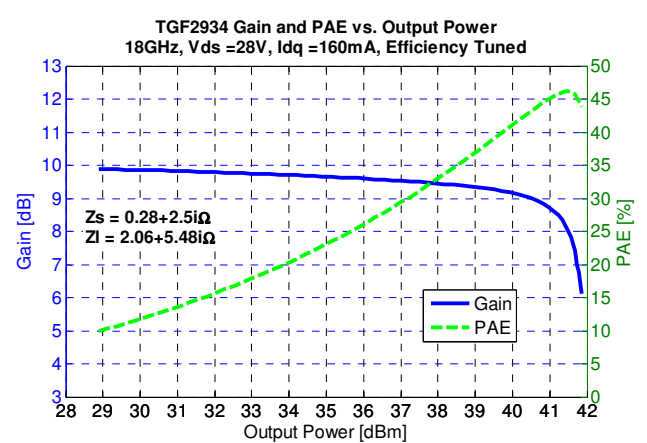
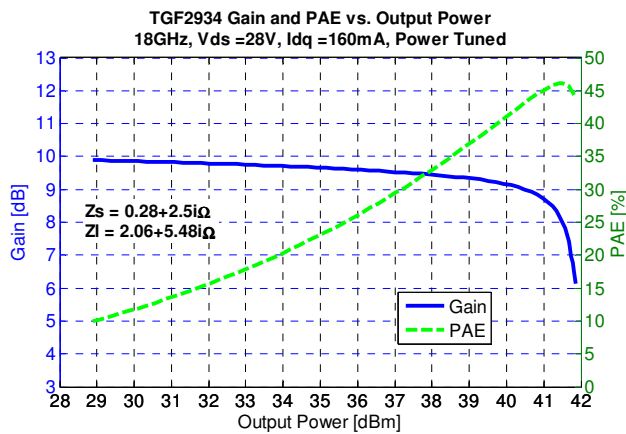
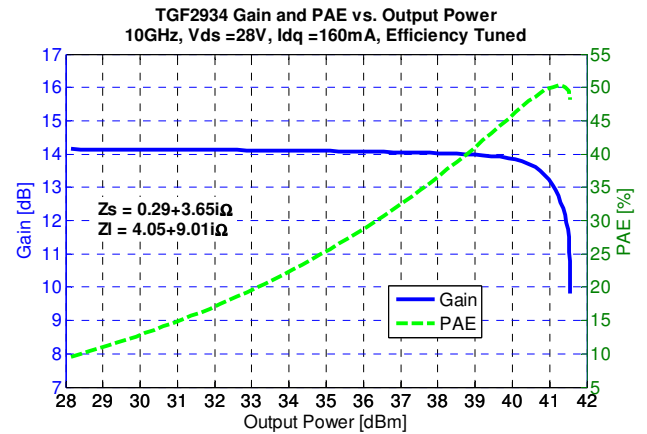
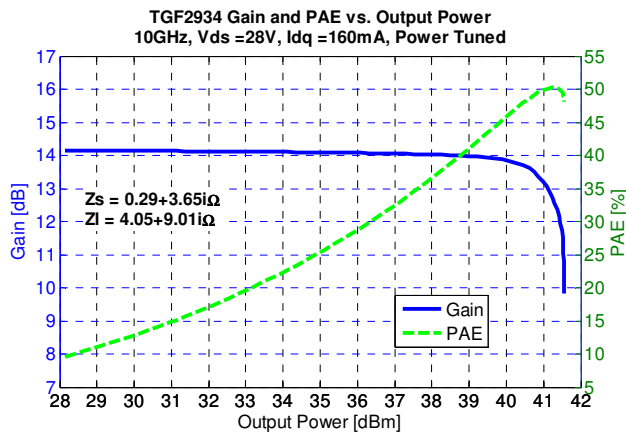
1. CW, Bondwires not included
2. See page 22 for load-pull and source-pull reference planes where the performance was measured.



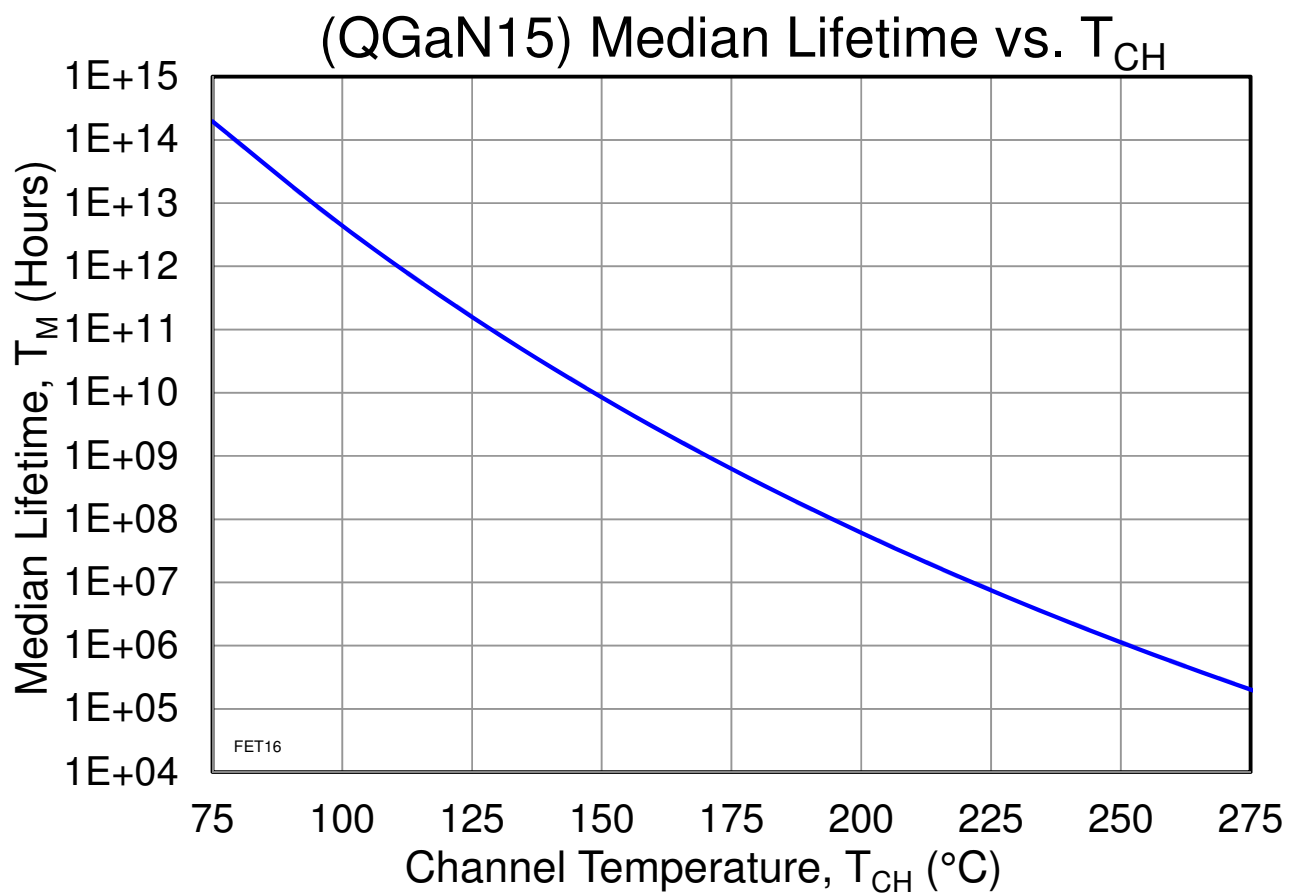
Typical Model Performance – Load-Pull Drive-up^{1,2}

Notes:

1. CW, Bondwires not included
2. See page 22 for load-pull and source-pull reference planes where the performance was measured.



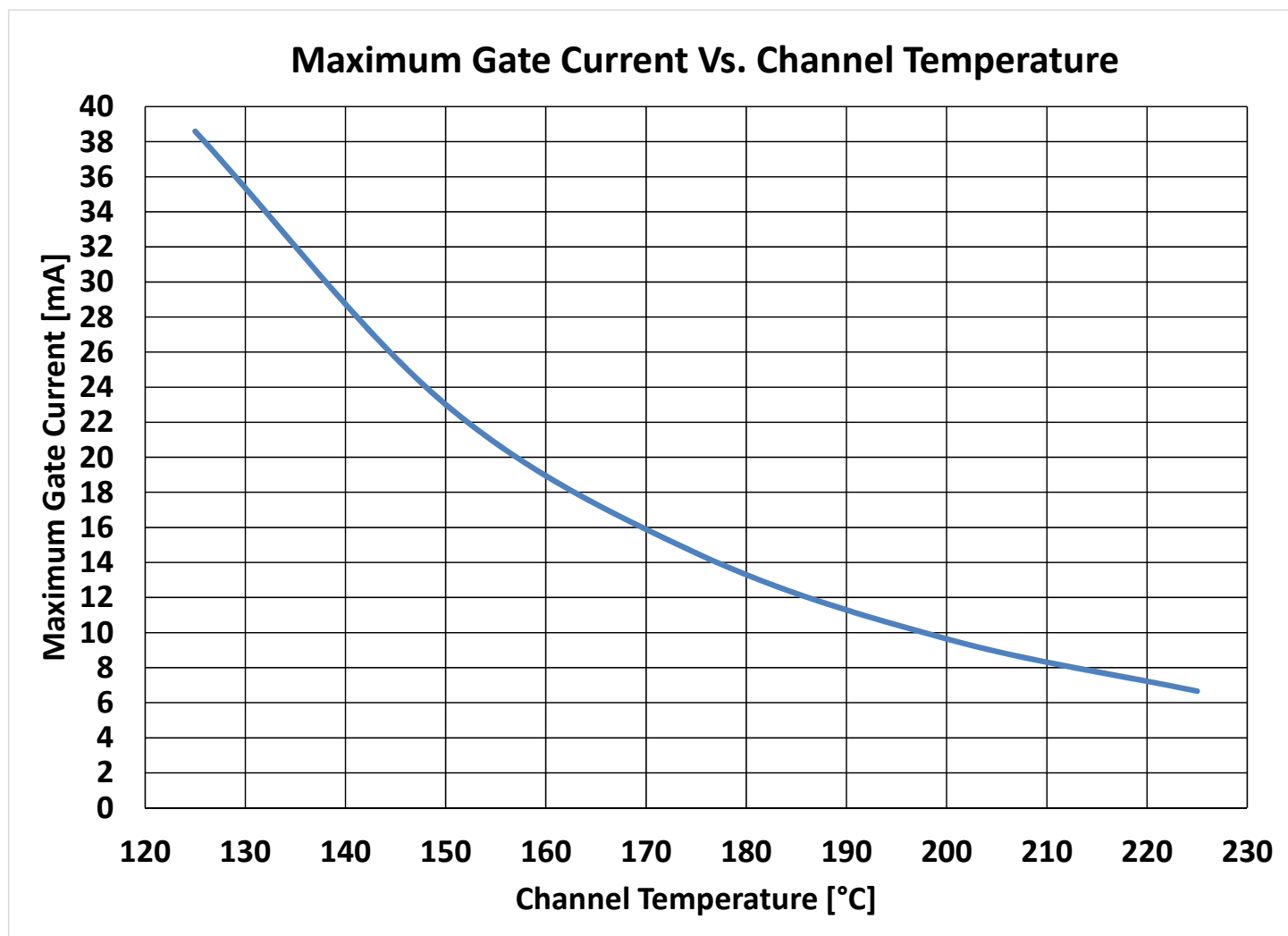
Median Lifetime¹



Notes:

1. Test Conditions: $V_D = +28$ V; Failure Criteria = 10 % reduction in I_{D_MAX} during DC Life Testing

Maximum Gate Current

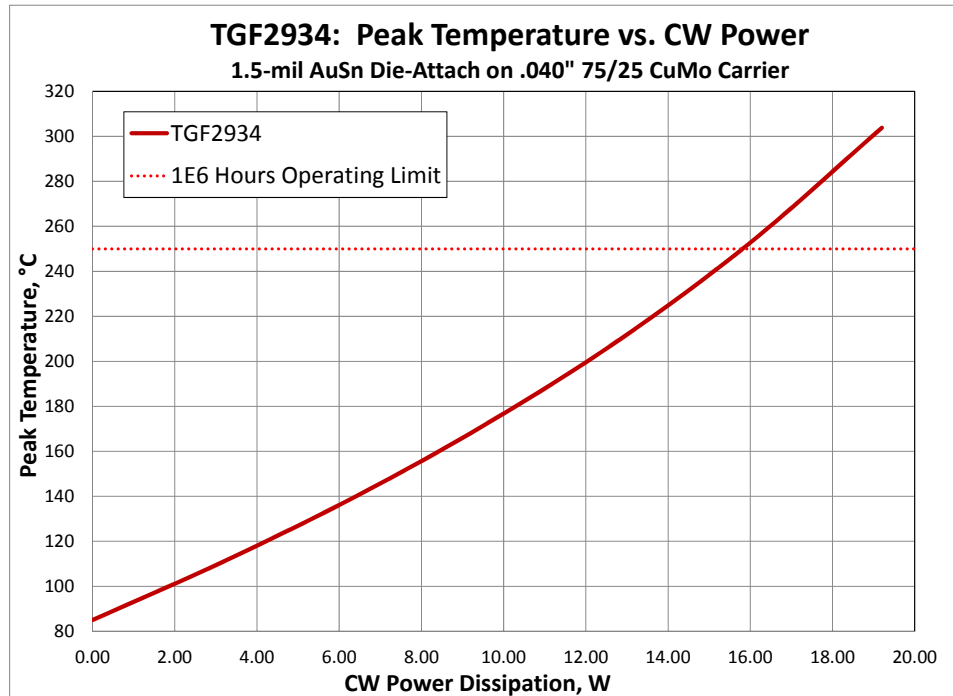


Thermal and Reliability Information

Parameter	Test Conditions	Value	Units
Thermal Resistance, θ_{JC} ⁽¹⁾	CW	8.1	°C/W
Channel Temperature, T_{CH}	$T_{baseplate} = +85\text{ °C}$	111	°C
Median Lifetime, T_M	$P_{DISS} = 3.2\text{ W}$	9.7E11	Hrs
Thermal Resistance, θ_{JC} ⁽¹⁾	CW	8.6	°C/W
Channel Temperature, T_{CH}	$T_{baseplate} = +85\text{ °C}$	140	°C
Median Lifetime, T_M	$P_{DISS} = 6.4\text{ W}$	2.6E10	Hrs
Thermal Resistance, θ_{JC} ⁽¹⁾	CW	9.1	°C/W
Channel Temperature, T_{CH}	$T_{baseplate} = +85\text{ °C}$	172	°C
Median Lifetime, T_M	$P_{DISS} = 9.6\text{ W}$	8.4E8	Hrs
Thermal Resistance, θ_{JC} ⁽¹⁾	CW	9.7	°C/W
Channel Temperature, T_{CH}	$T_{baseplate} = +85\text{ °C}$	209	°C
Median Lifetime, T_M	$P_{DISS} = 12.8\text{ W}$	2.8E7	Hrs
Thermal Resistance, θ_{JC} ⁽¹⁾	CW	10.5	°C/W
Channel Temperature, T_{CH}	$T_{baseplate} = +85\text{ °C}$	253	°C
Median Lifetime, T_M	$P_{DISS} = 16\text{ W}$	9.1E5	Hrs
Thermal Resistance, θ_{JC} ⁽¹⁾	CW	11.4	°C/W
Channel Temperature, T_{CH}	$T_{baseplate} = +85\text{ °C}$	304	°C
Median Lifetime, T_M	$P_{DISS} = 19.2\text{ W}$	3.3E4	Hrs

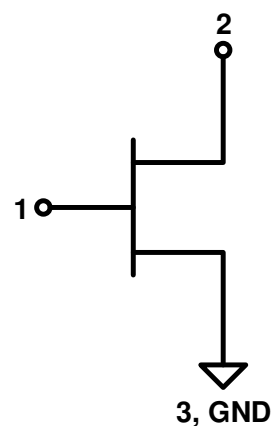
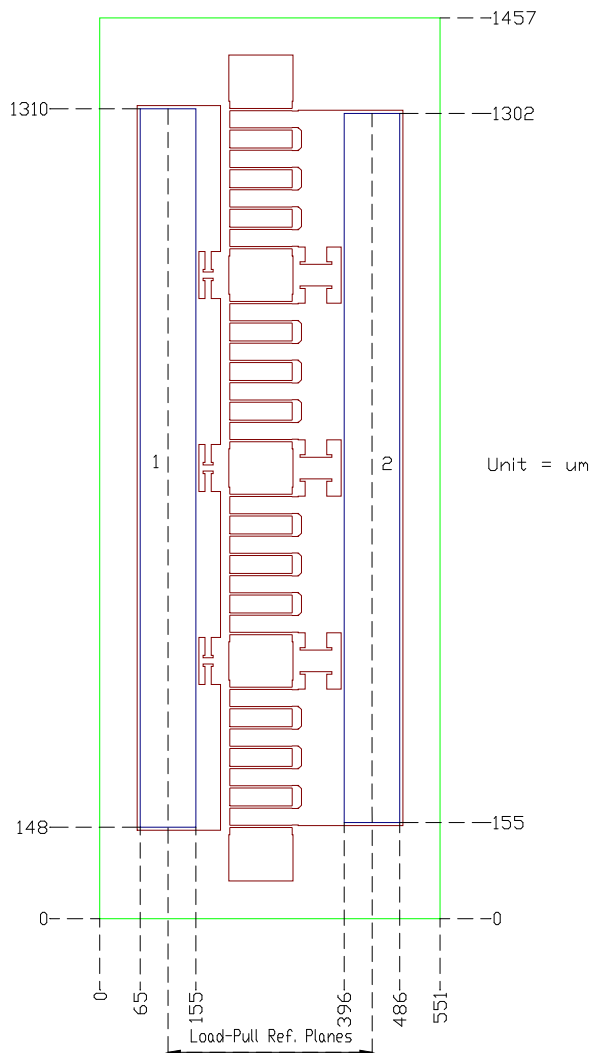
Notes:

1. Thermal resistance measured at back of package.



Pin Configuration and Description¹

Notes: 1. Die size tolerance is ± 0.015 mm.



Pin Description

Pin	Symbol	Description	Dimension
1	RF IN / V_G	Gate	1.162 x 0.090 mm
2	RF OUT / V_D	Drain	1.147 x 0.090 mm
3	Source	Source / Ground / Backside of die	1.457 x 0.551 mm

Assembly Notes

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment (i.e. epoxy) not recommended.

Reflow process assembly notes:

- Use AuSn (80/20) solder and limit exposure to temperatures above 300°C to 3-4 minutes, maximum.
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- Do not use any kind of flux.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Interconnect process assembly notes:

- Ball bonding is the preferred interconnect technique, except where noted on the assembly diagram.
- Force, time, and ultrasonics are critical bonding parameters.
- Aluminum wire should not be used.
- Devices with small pad sizes should be bonded with 0.0007-inch wire.

Disclaimer

GaN/SiC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

Bias-up Procedure

1. Set V_G to -4 V.
2. Set I_D limit to 200 mA.
3. Slowly adjust V_G until I_D reaches 160 mA.
4. Set I_D limit to 1200 mA.
5. Apply RF signal.

Bias-down Procedure

1. Turn off RF signal.
2. Turn off V_D and wait 1 second to allow drain capacitor discharge.
3. Turn off V_G .

Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	N/A	ESDA / JEDEC JS-001-2012
ESD – Charged Device Model (CDM)	N/A	JEDEC JESD22-C101F
MSL – Moisture Sensitivity Level	N/A	IPC/JEDEC J-STD-020



Caution!
ESD-Sensitive Device

Solderability

Compatible with both lead-free (260°C max. reflow temp.) and tin/lead (245°C max. reflow temp.) soldering processes.

Solder profiles available upon request.

Contact plating: NiPdAu

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- PFOS Free
- SVHC Free



Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations, and information about Qorvo:

Web: www.Qorvo.com
Email: info-sales@qorvo.com

Tel: +1.972.994.8465
Fax: +1.972.994.8504

For technical questions and application information: **Email:** info-products@qorvo.com

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Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331